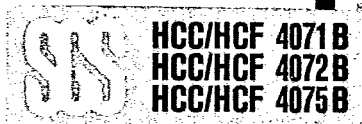


**COS/MOS
INTEGRATED
CIRCUITS**

41C 08878 DT-43-21

7929225 S G S SEMICONDUCTOR CORP

PRELIMINARY DATA

4071B - QUAD 2-INPUT OR GATE
 4072B - QUAD 4-INPUT OR GATE
 4075B - TRIPLE 3-INPUT OR GATE

- MEDIUM-SPEED OPERATION t_{PLH} , t_{PHL} = 60 ns. (TYP.) AT V_{DD} = 10V
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

The HCC 4071B/4072B and 4075B (extended temperature range) and HCF 4071B/4072B and 4075B (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package, ceramic flat package and plastic micropackage.

The HCC/HCF 4071B, 4072B and 4075B OR gates provide the system designer with direct implementation of the positive-logic OR function and supplement the existing family of COS/MOS gates.

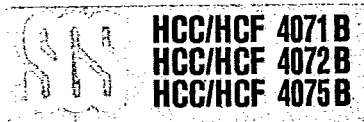
ABSOLUTE MAXIMUM RATINGS

V_{DD} *	Supply voltage: HCC types HCF types	-0.5 to 20 -0.5 to 18	V V
V_i	Input voltage	-0.5 to V_{DD} + 0.5	V
I_i	DC input current (any one input)	± 10	mA
P_{tot}	Total power dissipation (per package) Dissipation per output transistor for T_{op} = full package-temperature range	200 100	mW mW
T_{op}	Operating temperature: HCC types HCF types	-55 to 125 -40 to 85	°C °C
T_{stg}	Storage temperature	-65 to 150	°C

* All voltage values are referred to V_{SS} pin voltage

ORDERING NUMBERS:

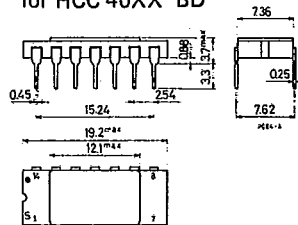
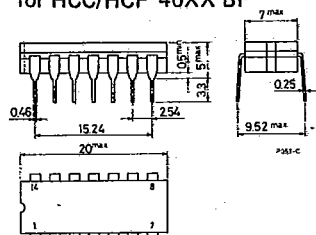
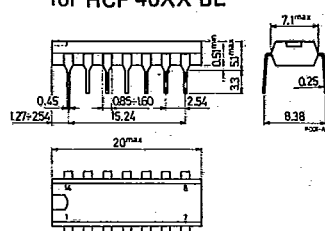
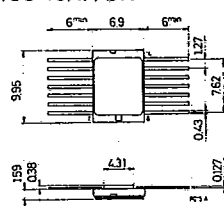
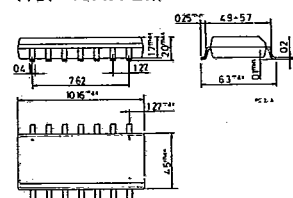
HCC 40XX BD for dual in-line ceramic package
 HCC 40XX BF for dual in-line ceramic package, frit seal
 HCC 40XX BK for ceramic flat package
 HCF 40XX BE for dual in-line plastic package
 HCF 40XX BF for dual in-line ceramic package, frit seal
 HCF 40XX BM for plastic micropackage



41C 08879 DT-43-21

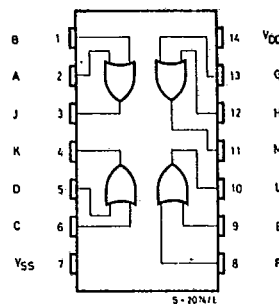
7929225 S G S SEMICONDUCTOR CORP

MECHANICAL DATA (dimensions in mm)

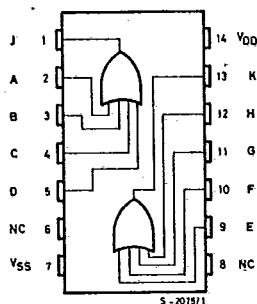
Dual in-line ceramic package
for HCC 40XX BDDual in-line ceramic package
for HCC/HCF 40XX BFDual in-line plastic package
for HCF 40XX BECeramic flat package for
HCC 40XX BKPlastic micropackage for
HCF 40XX BM

CONNECTION DIAGRAMS

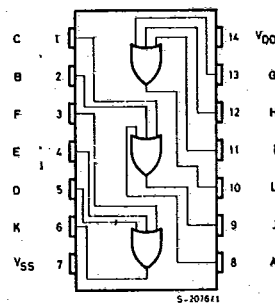
for 4071B



for 4072B



for 4075B



RECOMMENDED OPERATING CONDITIONS

V_{DD}	Supply voltage: HCC types HCF types	3 to 18 3 to 15	V V
V_I	Input voltage	0 to V_{DD}	V
T_{op}	Operating temperature: HCC types HCF types	-55 to 125 -40 to 85	°C °C

HCC/HCF 4071B
HCC/HCF 4072B
HCC/HCF 4075B

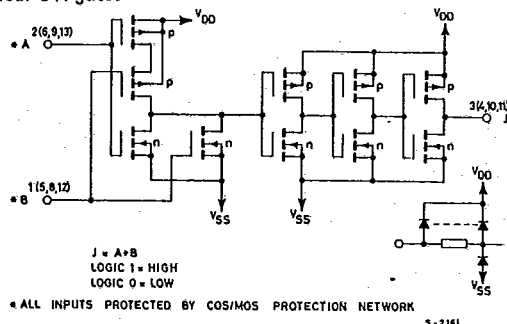
7929225 S G S SEMICONDUCTOR CORP

41C 08880

DT-43-21

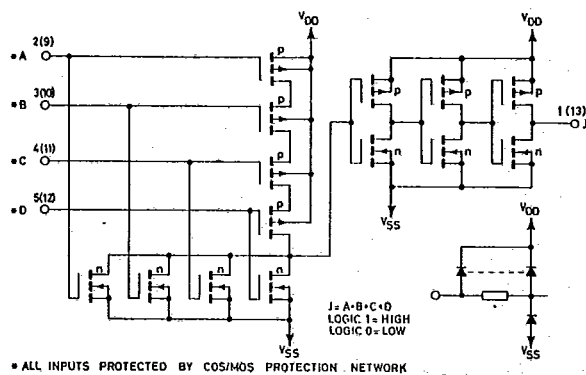
SCHEMATIC DIAGRAMS

For 4071B - 1 of 4 identical OR gates



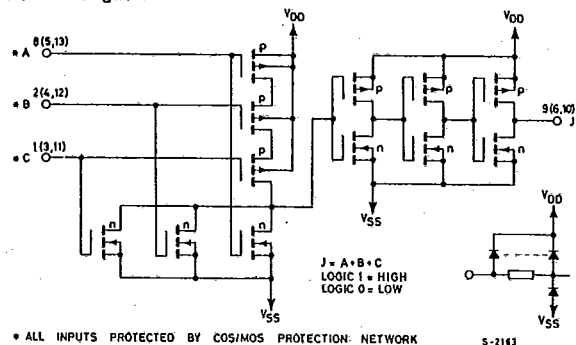
S-2161

For 4072B - 1 of 2 identical OR gates



S-2162

For 4075B - 1 of 3 identical OR gates



S-2163

HCC/HCF 4071B
HCC/HCF 4072B
HCC/HCF 4075B

41C 08881 07-43-21

7929225 S G S SEMICONDUCTOR CORP
STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Parameter			Test conditions				Values						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent current	HCC types	0/ 5			5		0.25		0.01	0.25		7.5	μA
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
	HCF types	0/ 5			5		1		0.01	1		7.5		
		0/10			10		2		0.01	2		15		
		0/15			15		4		0.01	4		30		
V _{OH}	Output high voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output low voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input high voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input low voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output drive current	HCC types	0/ 5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/ 5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
	HCF types	0/ 5	2.5		5	-1.53		-1.36	-3.2		-1.1			
		0/ 5	4.6		5	-0.52		-0.44	-1		-0.36			
		0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
I _{OL}	Output sink current	HCC types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
	HCF types	0/ 5	0.4		5	0.52		0.44	1		0.36			
		0/10	0.5		10	1.3		1.1	2.6		0.9			
		0/15	1.5		15	3.6		3.0	6.8		2.4			
I _{IH} , I _{IL}	Input leakage current	HCC types	0/18	Any input		18		±0.1		±10 ⁻⁵	±0.1		± 1	μA
		HCF types	0/15			15		±0.3		±10 ⁻⁵	±0.3		± 1	
C _I	Input capacitance		Any input							5	7.5			pF

* T_{Low} = - 55°C for HCC device; -40°C for HCF device.* T_{High} = +125°C for HCC device; +85°C for HCF device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5V
2V min. with V_{DD} = 10V
2.5V min. with V_{DD} = 15V

HCC/HCF 4071B
HCC/HCF 4072B
HCC/HCF 4075B

41C 08882

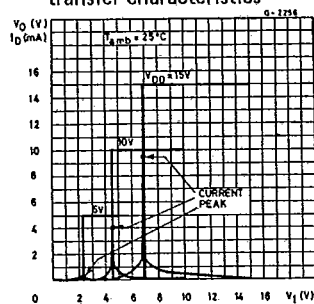
D7-43.21

7929225 S G S SEMICONDUCTOR CORP

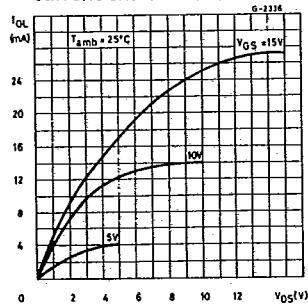
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20 ns)

Parameter	Test conditions	Values			Unit
		V_{DD} (V)	Min.	Typ.	Max.
t_{PHL} Propagation delay time		5		125	250
		10		60	120
		15		45	90
t_{PLH} Propagation delay time		5		175	350
		10		70	140
		15		50	110
t_{THL} , t_{TLH} Transition time		5		100	200
		10		50	100
		15		40	80

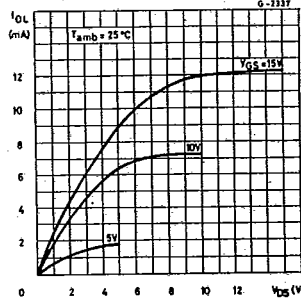
Typical voltage and current transfer characteristics



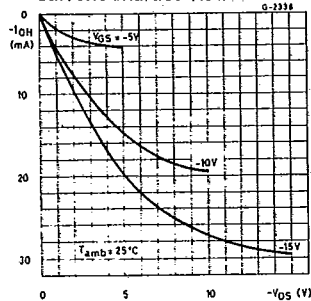
Typical output low (sink) current characteristics



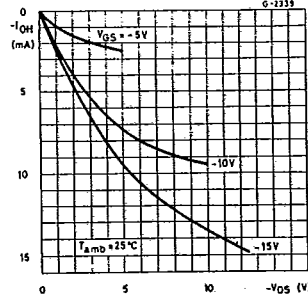
Minimum output low (sink) current characteristics



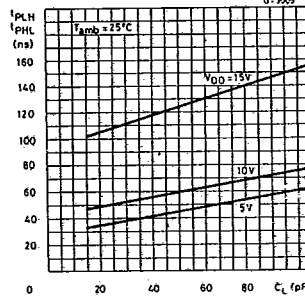
Typical output high (source) current characteristics



Minimum output high (source) current characteristics



Typical propagation delay time vs. load capacitance



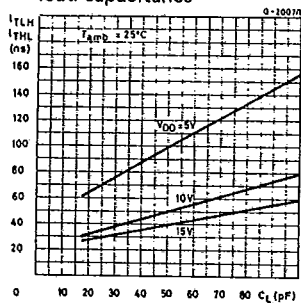
HCC/HCF 4071B
HCC/HCF 4072B
HCC/HCF 4075B

7929225 S G S SEMICONDUCTOR CORP

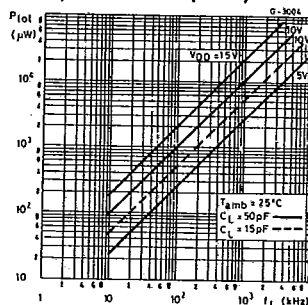
41C 08883

DT-43-21

Typical transition time vs.
load capacitance

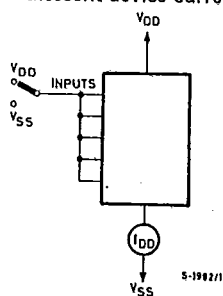


Typical dynamic power dis-
sipation vs. frequency

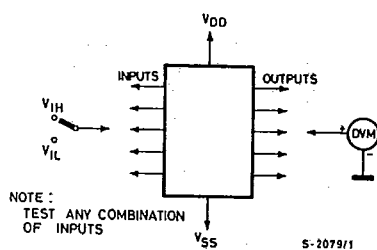


TEST CIRCUITS

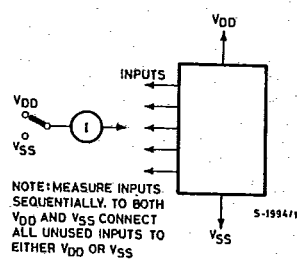
Quiescent device current

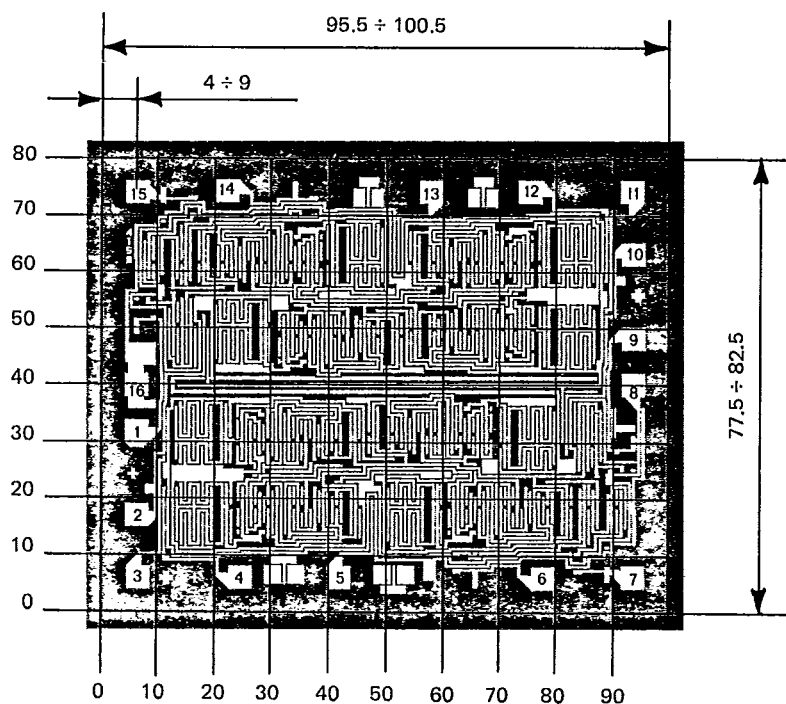


Input voltage

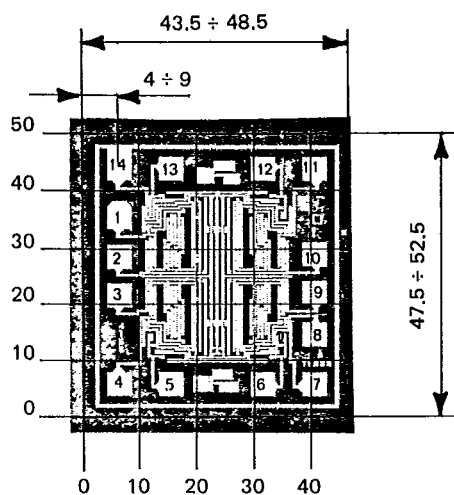


Input leakage current





4015B



4016B